PC	Number:	20190	426000.1	В			PCI	N Da	ate:	Aug.	13, 2019	
Titl	e: Qualific	cation of	TI Cheng	du A/T	Γ (CDA ⁻	T) as an A	Assembly	site	e for S	elect	Devices	
Cus	stomer Cont	act: P	CN Manage	<u>r</u> D)ept:	Qua	ality Serv	/ices	5			
Dro	posed 1 st Sl	nin Date		3, 201	10	Es	stimated		-		e provided at	t
	-		Aug.	5, 201			Ava	ilat	oility:	sam	ple request	
	ange Type:											
\square	Assembly Si				Design						np Site	
	Assembly Process				Data Sh			<u> </u>			np Material	
 Assembly Materials Mechanical Specification 						mber char	nge	\square			np Process	
	Packing/Shi				est Site est Pro			\mathbf{H}		er Fab	Materials	
	Packing/Shi	pping/La	Denny		est PIU	JLESS		\exists			Process	
					DCN	Details			vvare		FIOCESS	_
Dee	scription of	Change	•		FCN	Details						
Des		change	•									
the orig Tex Add	 PCN notification. These new devices are under Group 3 in the device list below. The expected first shipment date for these new devices will be 90 days from this notice (Oct 15, 2019) for these newly added devices only. The proposed 1st ship date of Aug 3, 2019 still applies for the original set of devices. Texas Instruments is pleased to announce the qualification of TI Chengdu (CDAT) as an Additional Assembly & Test site for the list of devices shown below. Current assembly sites and Material differences are as follows: 											
Gro	un 1 Device											
Gro	oup 1 Device	:	Carsen	n Suzł	hou	Ca	arsem S				CDAT	
								3				
M	oup 1 Device Iount Compo Iold compour	und	SID#	n Suzł 45514 44108	-3	SID	arsem S #435143 #435370			4	CDAT 207123 222198	
► ►	lount Compo lold compour	und Id	SID#	45514	-3	SID	#43514			4	207123	
► ►	lount Compo	und Id	SID#	45514	- <u>3</u> 6	SID	#435143 #435370)		4	207123	
► ►	lount Compo lold compour	und nd	SID# SID#	45514 44108	- <u>3</u> 36 Cla i	SID SID	0#435143 0#435370) CD/		4	207123	
~	lount Compo lold compour	und id es: Mount	SID# SID#	45514 44108	3 6 Cla 4207	SID SID rk 768	9#435143 9#435370 4) CD/ 207	123	4	207123	
► ►	lount Compo lold compour	und id es: Mount	SID# SID#	45514 44108	- <u>3</u> 36 Cla i	SID SID rk 768	9#435143 9#435370 4) CD/	123	4	207123	
Gro	lount Compour lold compour oup 2 Device	und nd es: Mount Mold c	SID# SID#	45514 44108	3 6 Cla 4207	SID SID rk 768	9#435143 9#435370 4) CD/ 207	123	4	207123	
Gro	lount Compo lold compour	und nd es: Mount Mold c	SID# SID#	45514 44108	.3 6 Cla 4207 4208	SID SID rk 768 625	0#435143 0#435370 4 4 4) CD/ 207 222	123 198	4	207123	
Gro	lount Compour lold compour oup 2 Device	und d es: Mount Mold c	SID# SID# compound	45514 44108	3 6 Cla 4207 4208 TIE	SID SID rk 768 625 M	0#435143 0#435370 4 4 4) CD/ 207 222	123 198 \T	4	207123	
Gro	lount Compour lold compour oup 2 Device	und d S: Mount Mold c Mold c	SID# SID# compound ompound	45514 44108	.3 66 Cla 4207 4208 4208 TIE 8095	SID SID rk 768 625 M 387	9#435143 9#435370 4 4 4) CD / 207 222 CD / 222	123 198 AT 198	4	207123	
Gro	lount Compour lold compour oup 2 Device	und d es: Mount Mold c	SID# SID# compound ompound	45514 44108	3 6 Cla 4207 4208 TIE	SID SID rk 768 625 M 387	9#435143 9#435370 4 4 4) CD/ 207 222	123 198 AT 198	4	207123	
Gro	lount Compour lold compour oup 2 Device	und d s: Mount Mold c s: Mold c Lead fi	SID# SID# compound ompound	45514 44108	.3 66 Cla 4207 4208 4208 TIE 8095	SID SID rk 768 625 M 387	9#435143 9#435370 4 4 4) CD / 207 222 CD / 222	123 198 AT 198	4	207123	
Gro	lount Compour lold compour oup 2 Device	und d es: Mount Mold c es: Mold c Lead fi	SID# SID# compound ompound	45514 44108	.3 66 Cla 4207 4208 4208 TIE 8095	SID SID rk 768 625 M 387	9#435143 9#435370 4 4 4) CD / 207 222 CD / 222	123 198 AT 198	4	207123	
Gro Gro Rea Con	10unt Compo 10ld compour 2 Device 2 Device 2 Device 2 Device 2 Device 2 Device 2 Device 2 Device 2 Device	und d es: Mount Mold c es: Mold c Lead fi oply	SID# SID# compound ompound nish	45514 44108	3 6 Cla 4207 4208 TIE 8095 Matte	SID SID 768 625 M 387 2 Sn	0#435143 0#435370 4 4 4 4	CD/ 207 222 CD/ 222 NiPd	123 198 AT 198 Au	4	207123 222198	
Gro Gro Rea Con Ant	Iount Compour Iold compour oup 2 Device oup 3 Device ason for Cha atinuity of Sup cicipated imp	und d es: Mount Mold c es: Mold c Lead fi oply	SID# SID# compound ompound nish	45514 44108	3 6 Cla 4207 4208 TIE 8095 Matte	SID SID 768 625 M 387 2 Sn	0#435143 0#435370 4 4 4 4	CD/ 207 222 CD/ 222 NiPd	123 198 AT 198 Au	4	207123 222198):
Gro Gro Rea Con Ant	Iount Compo Iold compour oup 2 Device oup 3 Device ason for Cha atinuity of Sup icipated impose	und d es: Mount Mold c es: Mold c Lead fi oply pact on	SID# SID# compound ompound nish Form, Fit	45514 44108	3 6 207 4207 4208 5 4208 5 7 7 8095 8095 Matte	SID SID 768 625 M 387 2 Sn Quality (0#435143 0#435370 4 4 4 4	CD/ 207 222 CD/ 222 NiPd	123 198 AT 198 Au	4	207123 222198):
Gro Gro Rea Con Ant	Iount Compour Iold compour oup 2 Device oup 3 Device ason for Cha atinuity of Sup icipated impose icipated impose	Mount Mold c Mold c Mold c Mold c Lead fi Deply pact on	SID# SID# compound ompound nish Form, Fit	45514 44108	.3 6 Clar 4207 4208 7 TIE 8095 Matte	SID SID SID rk 768 625 M 387 2 Sn Quality o	9#435143 9#435370 4 4 4 4 4	CD/ 207 222 CD/ 222 NiPd	123 198 AT 198 Au y (pos	4 4 sitive	207123 222198 • / negative):
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Gro Gro Rea Con Ant	Iount Compour Iold compour oup 2 Device oup 3 Device ason for Cha atinuity of Sup cicipated imple icipated imple	und d es: Mount Mold c es: Mold c Lead fi oply pact on to the	SID# SID# compound ompound nish Form, Fit Material	45514 44108 d d t, Fun becla laterial rom pro	Clar 4207 4208 4208 TIE 8095 Matte	SID SID SID rk 768 625 M 387 2 Sn Quality of rations or on data ar ease. Upo	9#435143 9#435370 4 4 4 4 4 4 4 4 4 4 5 7 8 7 8 7 8 9 7 8 9 7 9 7 9 7 9 7 9 7 9	CD/ 207 2222 CD/ 2222 NiPd	123 198 AT 198 Au y (pos itent r ailable n relea	4 4 sitive	207123 222198 • / negative s are driven ving the	
Gro Gro Rea Con Ant	Iount Compour Iold compour oup 2 Device oup 3 Device ason for Cha atinuity of Sup cicipated imple icipated imple	und d es: Mount Mold c es: Mold c Lead fi oply pact on to the	SID# SID# compound ompound nish Form, Fit	45514 44108 d d t, Fun laterial rom pro roduct eports	Clar 4207 4208 4208 TIE 8095 Matte	SID SID SID rk 768 625 M 387 2 Sn Quality of rations or on data ar ease. Upo e obtained	e#435143 e#435370 4 4 4 4 4 4 4 4 4 4 4 4 4 5 7 7 8 7 8 7 8 7 8 7 8 7 8 7 8 7 8 7 8	CD/ 207 222 CD/ 222 NiPd Dilit	123 198 AT 198 Au y (pos ailable n releating	4 4 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9	207123 222198 e / negative s are driven ving the e revised	
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Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
TI Clark	QAB	PHL	Angeles City, Pampanga
Carsem S	CRS	MYS	Jelapang
Carsem Suzhou	CSZ	CHN	Jiangsu
CDAT	CDA	CHN	Chengdu
MADE IN: Malaysia 2DC: 20: MSL 2 /260C/1 YEAR SE		(Q) 2000 (D) 0336 (311) LOT: 3959047MLA (4W) TKY (1T) 75234838	
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OPT: ITEM: 3	9	(P) (2P) REV: (V) 00333 (2 <u>0L) CSO:SHE</u> (21L) CCO:US	17 6A
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roduct Affected: roup 1 Devices: SN0803054DRCR	1750	(P) (2P) REV: (V) 00333 (20L) CSO: SHE (21L) CCO:US (22L) ASO: MLA (23L) ACO: M	17 6A
roduct Affected: roup 1 Devices: SN0803054DRCR roup 2 Devices:	1750	(P) (2P) REV: (V) 00333 (20L) CSO: SHE (21L) CCO:US (22L) ASO: MLA (23L) ACO: M	17 6A
Devices: Toup 1 Devices: SN0803054DRCR roup 2 Devices: TPS65233RTER	1750 SN75LVCP601RTJ	(P) (2P) REV: (V) 00333 (20L) CSO: SHE (21L) CCO:US (22L) ASO: MLA (23L) ACO: M	17 6A
OPT: 3 ITEM: 3 LBL: 5A (L)TO: roup 1 Devices: 3 SN0803054DRCR roup 2 Devices: TPS65233RTER roup 3 Devices:	1750 SN75LVCP601RTJ TPS65233RTET	(P) (2P) REV: (V) 00333 (20L) CSO: SHE (21L) CCO:US (22L) ASO: MLA (23L) ACO: M R SN75LVCP601RTJT	17 5A YS
roup 1 Devices:	1750 SN75LVCP601RTJ TPS65233RTET PB LP8556SQE-E00/NG	(P) (2P) REV: (V) 00333 (20L) CS0: SHE (21L) CC0:US (22L) AS0: MLA (23L) AC0: M R SN75LVCP601RTJT DPB LP8556SQX-E00/I	17 5A YS]]

Group 1 Devices Qual Memo:

Qua	lification	Results

	Data Displayed as: Number of lots / Total sample size / Total failed						
Туре	Test Name / Condition	Duration	QBS Package Reference: <u>BQ294504DRV</u>	QBS Package Reference: <u>TRS3122ERGE</u>	QBS Package Reference: <u>BQ24196RGE</u>	QBS Package Reference: <u>TPS51285BRUK</u>	QBS Package Reference: <u>TPS53641RSB</u>
AC	Autoclave 121C	96 Hours	3/231/0	3/231/0	3/231/0	3/231/0	3/231/0
ED	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	-	-	-
HAST	Biased HAST, 130C/85%RH	96 Hours	3/231/0	3/231/0	-	-	-
HTOL	Life Test, 150C	300 Hours	-	1/77/0	-	-	-
HTSL	High Temp. Storage Bake, 150C	1000 Hours	-	3/231/0	-	-	-
HTSL	High Temp. Storage Bake, 170C	420 Hours	-	-	-	-	3/231/0
SD	Solderability	Pb Free	-	1/22/0	-	-	-
TC	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0	3/231/0	3/231/0	3/231/0
UHAST	Unbiased HAST, 110C/85%RH	264 Hours	-	-	-	-	-
WBP	Bond Pull	Wires	3/228/0	3/228/0	3/228/0	3/228/0	3/228/0
WBS	Ball Bond Shear	Wires	3/228/0	3/228/0	3/228/0	3/228/0	3/228/0

 WBS
 Ball Bond Shear
 Wires
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Qualification Report

Approve Date 07-June-2019

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

	Data Displayed as. Number of lots / Total sample size / Total failed							
Туре	Test Name / Condition	Duration	Qual Device: <u>SN75LVCP601RTJR/</u> <u>T</u>	Qual Device: <u>HD3SS460RNH</u>	QBS Process Reference: <u>HD3SS3411TRWAQ1</u>			
AC	Autoclave 121C	oclave 121C 96 Hours		1/77/0	3/231/0			
ED	Electrical Characterization	Per Datasheet Parameters	-	Pass	Pass			
ELFR	Early Life Failure Rate, 140C	24 Hours	-	-	3/2400/0			
HAST	Biased HAST, 130C/85%RH	96 Hours	-	-	3/231/0			
HBM	ESD - HBM	4000 V	-	1/3/0	1/3/0			
CDM	ESD - CDM	1500 V	-	1/3/0	1/3/0			
HTOL	Life Test, 140C	480 Hours	-	-	3/231/0			
HTSL	High Temp. Storage Bake, 150C	1000 Hours	-	3/231/0	2/90/0			
LU	Latch-up 90C	(per JESD78)	-	1/6/0	1/6/0			
LU	Latch-up 25C	(per JESD78)		1/6/0	1/6/0			
PD	Physical Dimensions	Cpk>1.67	1/5/0	3/15/0	3/30/0			
SD	Surface Mount Solderability	Pb Free	1/22/0	3/15/0	1/15/0			
SD	Surface Mount Solderability	Pb	1/22/0	3/15/0	1/15/0			
тс	Temperature Cycle, - 65/150C	500 Cycles	1/77/0	1/77/0	3/231/0			
MQ	Manufacturing Assembly	(per mfg. Site specification)	Pass	Pass	Pass			
BPC	Bond Pad Cratering Check			3/6/0				
TPI	Thermal Path Integrity	Level 2-260C(+5/-0C)		3/26/0	-			
UHAS T	Unbiased HAST, 130C/85%RH	96 Hours	-	3/231/0	-			
WBP	Bond Pull	Wires	1/76/0	3/228/0	3/228/0			
WBS	Ball Bond Shear	Wires	1/76/0	3/228/0	3/228/0			
VQR	Visual Quality Reliability Inspection	Post 500 Temp Cycle	1/2/0	1/2/0	-			

- QBS: Qual By Similarity

- Qual Devices qualified at LEVEL2-260C: HD3SS460IRNH, HD3SS460RNH

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

THIS INFORMATION RELATING TO QUALITY AND RELIABILITY IS PROVIDED "AS IS." Product information detailed in this report may not accurately reflect TI's current product materials, processes and testing used in the construction of the TI products. Customers are solely responsible to conduct sufficient engineering and additional qualification testing to determine whether a device is suitable for use in their applications. Using TI products outside limits stated in TI's datasheet may void TI's warranty. See TI's Terms of Sale at "http://www.ti.com/lsds/ti/legal/termsofsale.page"

Group 2 Devices Qual Memo: Qualification Results

Туре	Test Name / Condition	Duration	Qual Device: TPS65233RTE	QBS Package Reference: <u>BQ24196RGER</u>	QBS Package Reference: <u>TPS54678RTE</u>
ED	Electrical Characterization	Per Datasheet Parameters	-	-	-
ED	Electrical Characterization, side by side	-	Pass	-	Pass
HBM	ESD - HBM	4000 V	-	-	-
HBM	ESD - HBM	2000 V	-	-	-
CDM	ESD - CDM	1500 V	-	-	1/3/0
CDM	ESD - CDM	1000 V	-	-	-
CDM	ESD - CDM	750 V	-	-	-
LU	Latch-up	(per JESD78)	-	-	-
MM	ESD - MM	100 V	-	-	-
HTOL	Life Test, 125C	1000 Hours	-	-	-
HTSL	HTSL High Temp Storage Bake, 10 150C 11		-	-	-
HAST	Biased HAST, 130C/85%RH	96 Hours	-	-	-
AC	Autoclave 121C	96 Hours	-	3/231/0	-
TC	Temperature Cycle, -65/150C	500 Cycles	-	3/231/0	-
TS	Thermal Shock, -65/150C	500 Cycles	-	-	-
WBP	Bond Pull	Wires	-	3/228/0	-
WBS	Ball Bond Shear	Wires	-	3/228/0	-

Data Displayed as: Number of lots / Total sample size / Total failed

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
 The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

Group 3 Qualification Report

Approve Date 26-June-2019

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Typ e	Test Name / Condition	Duration	Qual Device: LP8556SQE0WZ8 5	QBS Product/Proces s Reference: LP8556TMX- E09/S1	QBS Package Reference: TPS53641RSB R	QBS Package Reference: TPS51285BRUK R	QBS Package Reference: TRS3122ERGE R
AC	Autoclave	96 Hours	1/77/0	-	3/231/0	3/231/0	3/231/0
ED	Electrical Characterization	(Per Datasheet Parameters)	1/30/0	-	-	-	3/90/0
	Early Life Failure Rate, 125C	48 Hours	-	3/913/0	-	-	-
HBM	ESD - HBM	1000 V	1/77/0	1/3/0	-	-	-
HBM	ESD - HBM	2500 V	-	1/3/0	-	-	-
CDM	ESD - CDM	1000 V	-	1/3/0	-	-	-
CDM	ESD - CDM	1500 V	1/3/0	-	-	-	-
HAST	Biased HAST, 130C/85%RH	96 Hours	-	2/154/0	-	-	3/231/0
HAST	Biased HAST, 110C/85%RH	264 Hours	-	1/77/0	-	-	-
HTOL	Life Test, 125C	1000 Hours	_	3/228/0	-	-	-

HTSL	High Temp. Storage Bake, 170C	420 Hours	1/77/0	-	3/231/0	-	-
HTSL	High Temp. Storage Bake, 150C	1000 Hours	-	1/77/0	-	-	-
LU	Latch-up	(per JESD78) 25C	-	3/18/0	-	-	-
LU	Latch-up	(per JESD78) 125C	-	3/18/0	-	-	-
тс	Temperature Cycle, -65/150C	500 Cycles	1/77/0	3/231/0	3/231/0	3/231/0	3/231/0
тнвт	Temp Humidity 85C/85%Rh	1000 Hours	-	-	-	-	-
uHAS T	unBiased HAST, 130C/85%RH	96 Hours	1/77/0	3/231/0	-	-	-
WBP	Bond Pull	76 Wires, 3 units min	-	-	3/228/0	3/228/0	3/228/0
WBS	Ball Bond Shear	76 Wires, 3 units min	-	-	3/228/0	3/228/0	3/228/0
MQ	Manufacturability (Assembly)	(Per Mfg. Site Specification)	3/Pass	-	-	-	-

- QBS: Qual By Similarity

- Qual Device LP8556SQE0WZ85//NOPB is qualified at LEVEL1-260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

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